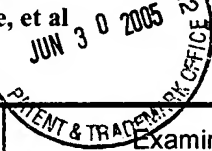


TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**(Under 37 CFR 1.97(b) or 1.97(c))**Docket No.
YOR920030293US1In Re Application Of: **Kwang Su Choe, et al**

Application No.

Filing Date

Examiner

Customer No.

Group Art Unit

Confirmation No.

10/674,647

September 30, 2003

Unknown

23389

1753

4796

Title: **THIN BURIED OXIDES BY LOW-DOSE OXYGEN IMPLANTATION INTO MODIFIED SILICON**

Address to:

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**37 CFR 1.97(b)**

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

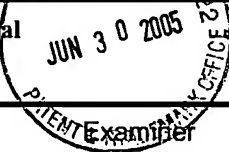
2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);**OR**☐ the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
YOR920030293US1

In Re Application: Kwang Su Choe, et al



Application No. 10/674,647	Filing Date September 30, 2003	Examiner Unknown	Customer No. 23389	Group Art Unit 1753	Confirmation No. 4796
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Title: THIN BURIED OXIDES BY LOW-DOSE OXYGEN IMPLANTATION INTO MODIFIED SILICON

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- ☐ A check in the amount of _____ is attached.
- ☒ The Director is hereby authorized to charge and credit Deposit Account No. 50-0510/IBM as described below.
- ☐ Charge the amount of _____
- ☒ Credit any overpayment.
- ☒ Charge any additional fee required.
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WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

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June 28, 2005

(Date)

Signature of Person Mailing Correspondence

Leslie S. Szivos
Typed or Printed Name of Person Mailing Certificate

*This certificate may only be used if paying by deposit account.

Signature

Dated: June 28, 2005

Leslie S. Szivos
Registration No. 39,394

SCULLY, SCOTT, MURPHY & PRESSER
400 Garden City Plaza, Suite 300
Garden City, New York 11530
(516) 742-4343

CC:



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Kwang Su Choe, et al.

Examiner: Unknown

Serial No.: 10/674,647

Art Unit: 1753

Filed: September 30, 2003

Docket: YOR920030293US1 (16818)

For: THIN BURIED OXIDES BY LOW-DOSE
OXYGEN IMPLANTATION INTO MODIFIED
SILICON

Dated: June 28, 2005

Confirmation No: 4796

Mailstop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT


Sir:

In accordance with 37 C.F.R. §1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case:

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on June 28, 2005.

Dated: June 28, 2005



Leslie S. Szivos

1. U.S. Patent Application Publication No. US 2002/0086463 A1, published July 4, 2002, to Houston, et al.;

2. U.S. Patent Application Publication No. US 2004/0126985 A1, published July 1, 2004, to Bendernagel, et al.;

3. Japanese Patent Application No. 9-64323, dated July 3, 1997;

4. International Patent Application No. WO 2005/034209 A2, dated April 14, 2005; and

5. Matsumura, et al., "Technological innovation in low-dose SIMOX wafers fabricated by an internal thermal oxidation (ITOX) process", 2002 Elsevier Science B.V., Microelectronic Engineering 66 (2003), pp. 400-414.

The references, which were cited in an International Search Report received from the European Patent Office dated March 21, 2005, are being submitted herewith, with a copy of the International Search Report. The International Search Report is from the corresponding PCT application which was filed on September 28, 2004 as PCT/US2004/031823. The relevance of the above-identified references have been described in the Search Report.

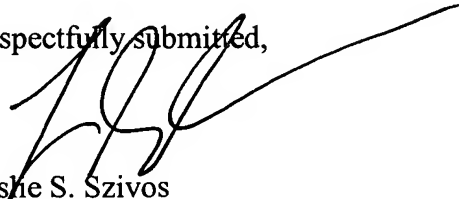
Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

In the event that an Office Action on the merits issues and crosses in the mail with this submission, the applicants hereby state:

That each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office on a counterpart foreign application not more than three months prior to the filing of this statement.

Consideration and entry of record of this information disclosure statement are thus respectfully requested.

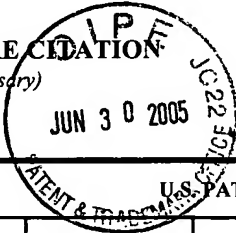
Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Leshe S. Szivos', written over the text 'Respectfully submitted,'.

Leshe S. Szivos
Registration No. 39,394

Scully, Scott, Murphy & Presser
400 Garden City Plaza, Suite 300
Garden City, New York 11530
(516) 742-4343

LSS:gc

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) YOR920030293US1 (16818)		Application Number 10/674,647		
				Applicant(s) Kwang Su Choe, et al.				
				Filing Date September 30, 2003		Group Art Unit 1753		
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
U.S. PATENT APPLICATION PUBLICATIONS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
		US 2002/0086463 A1	07/04/02	Houston, et al				
		US 2004/0126985 A1	07/01/04	Bendernagel, et al				
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
		9-64323	07/03/97	Japan				
		WO 2005/034209 A2	04/15/05	PCT				
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
		Matsumura, et al., "Technological innovation in low-dose SIMOX wafers fabricated by an internal thermal oxidation (ITOX) process", 2002 Elsevier Science B.V., Microelectronic Engineering 66 (2003), pp. 400-414						
EXAMINER				DATE CONSIDERED				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								